# imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

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## **RF & MICROWAVE TRANSISTORS HF SSB APPLICATIONS**

#### Features

- 30 MHz
- 50 VOLTS
- **P**<sub>OUT</sub> = 250 WATTS
- $G_P = 14.5 \text{ dB MINIMUM}$
- IMD = -30 dB
- GOLD METALIZATION
- COMMON EMITTER CONFIGURATION

### DESCRIPTION:

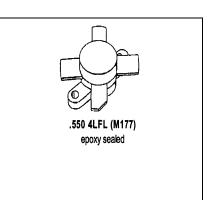
The MS1004 is a 50V epitaxial silicon NPN planar transistor designed primarily for SSB and VHF communications. This device utilizes emitter ballasting for improved ruggedness and reliability.

## ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

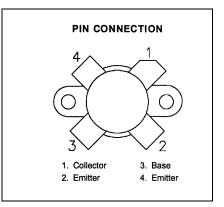
Symbol	Parameter	Value	Unit	
V <sub>сво</sub>	Collector-Base Voltage	110	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	55	V	
V <sub>EBO</sub>	Emitter-Base Voltage	4.0	V	
lc	Device Current	40	Α	
P <sub>DISS</sub>	Total Dissipation	330	W	
TJ	Junction Temperature	200	°C	
Т <sub>stg</sub>	Storage Temperature	-65 to +150	°C	

#### Thermal Data

R <sub>TH(J-C)</sub>	Thermal Resistance Junction-case	0.4	°C/W
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**MS1004** 





## MS1004

## ELECTRICAL SPECIFICATIONS (Tcase = $25^{\circ}$ C)

#### STATIC

Symbol	Test Conditions		Value			
			Min.	Typ.	Max.	Unit
BV <sub>CES</sub>	I <sub>c</sub> = 200 mA	$V_{BE} = 0 V$	110			V
BV <sub>CEO</sub>	I <sub>c</sub> = 200 mA	I <sub>B</sub> = 0 mA	55			V
BV <sub>EBO</sub>	I <sub>E</sub> = 20 mA	I <sub>c</sub> = 0 mA	4.0			V
I <sub>CEO</sub>	$V_{CE} = 30 V$	l <sub>E</sub> = 0 mA			10	mA
I <sub>CES</sub>	V <sub>CE</sub> = 60 V	Ι <sub>Ε</sub> = 0 mA			10	mA
h <sub>FE</sub>	V <sub>CE</sub> = 6 V	I <sub>c</sub> = 10 A	15		45	

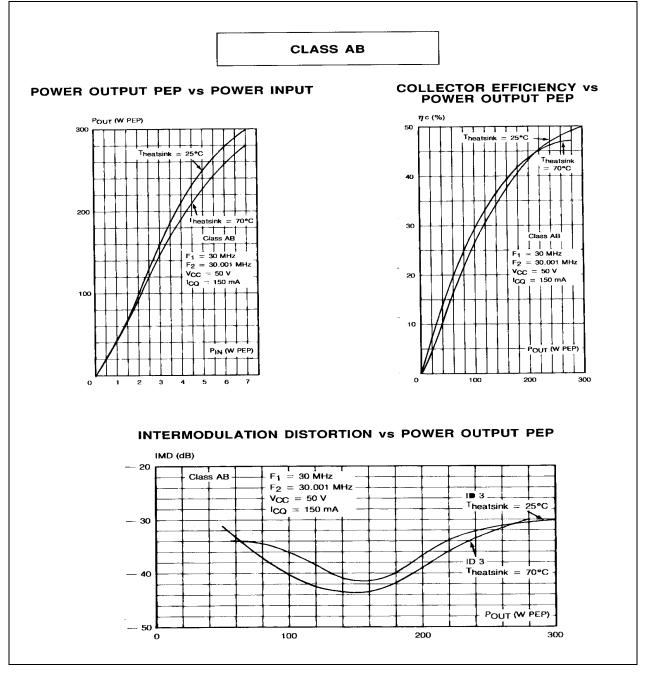
#### DYNAMIC

Symbol	Test Conditions			Value			
Symbol	Test Conditions			Min.	Typ.	Max.	Unit
Pout	f = 30MHz	$V_{cc} = 50 V$	I <sub>CQ</sub> =150 mA	250			WPEP
G <sub>P</sub>	f = 30MHz	$V_{cc} = 50 V$	I <sub>CQ</sub> =150 mA	14.5			dB
IMD*	f = 30MHz	$V_{CC} = 50 V$	I <sub>CQ</sub> =150 mA			-30	dBc
η <sub>c</sub>	f = 30MHz	$V_{cc} = 50 V$	I <sub>CQ</sub> =150 mA	37			%
Сов	f = 1 MHz	$V_{CB}$ =50 V				360	pf
Condition	f1 = 30.000 MHz	f2 = 30.001	MHz				



## MS1004

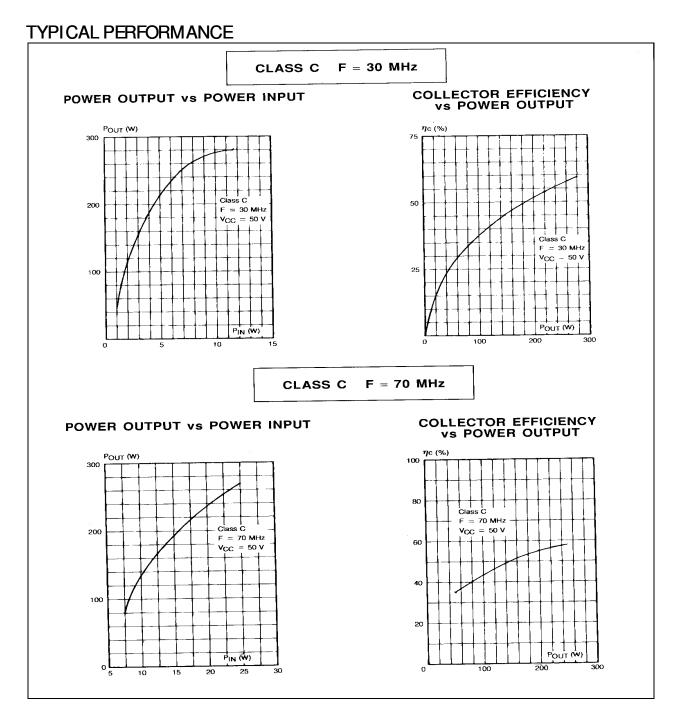
#### **TYPICAL PERFORMANCE**



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## MS1004



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## MS1004

